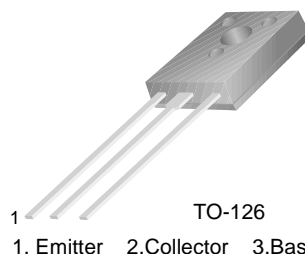


## BD375/377/379

### Medium Power Linear and Switching Applications

- Complement to BD376, BD378 and BD380 respectively

### NPN Epitaxial Silicon Transistor



TO-126  
1. Emitter 2. Collector 3. Base

### Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage : BD375	50	V
	: BD377	75	V
	: BD379	100	V
$V_{CEO}$	Collector-Emitter Voltage : BD375	45	V
	: BD377	60	V
	: BD379	80	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current (DC)	2	A
$I_{CP}$	*Collector Current (Pulse)	3	A
$I_B$	Base Current	1	A
$P_C$	Collector Dissipation ( $T_C=25^\circ\text{C}$ )	25	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	- 55 ~ 150	$^\circ\text{C}$

### Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$V_{CEO(sus)}$	* Collector-Emitter Sustaining Voltage	$I_C = 100\text{mA}, I_B = 0$	45			V
	: BD375					
	: BD377					
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = 100\mu\text{A}, I_E = 0$	50			V
	: BD377					
	: BD379					
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = 45\text{V}, I_E = 0$ $V_{CB} = 60\text{V}, I_E = 0$ $V_{CB} = 80\text{V}, I_E = 0$			2	$\mu\text{A}$
	: BD375					
	: BD377					
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = 5\text{V}, I_C = 0$			100	$\mu\text{A}$
$h_{FE1}$	* DC Current Gain	$V_{CE} = 2\text{V}, I_C = 0.15\text{A}$	40		375	
$h_{FE2}$						
$V_{CE(sat)}$	* Collector-Emitter Saturation Voltage	$I_C = 1\text{A}, I_B = 0.1\text{A}$			1	V
$V_{BE(on)}$	* Base-Emitter ON Voltage	$V_{CE} = 2\text{V}, I_C = 1\text{A}$			1.5	V
$t_{ON}$	Turn ON Time	$V_{CC} = 30\text{V}, I_C = 0.5\text{A}$ $I_{B1} = - I_{B2} = 0.05\text{A}$ $R_L = 60\Omega$		50		ns
$t_{OFF}$	Turn OFF Time					

\* Pulse Test: PW=350 $\mu\text{s}$ , duty Cycle=2% Pulsed

### $h_{FE}$ Classification

Classification	6	10	16	25
$h_{FE1}$	40 ~ 100	63 ~ 160	100 ~ 250	150 ~ 375

# Typical Characteristics

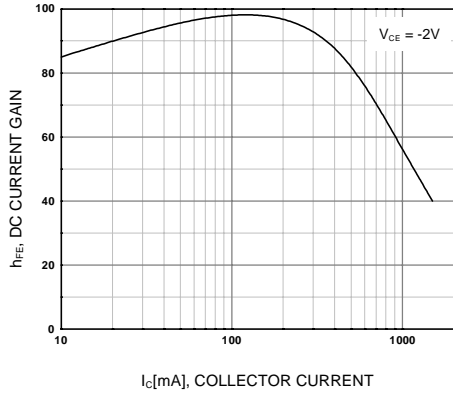


Figure 1. DC current Gain

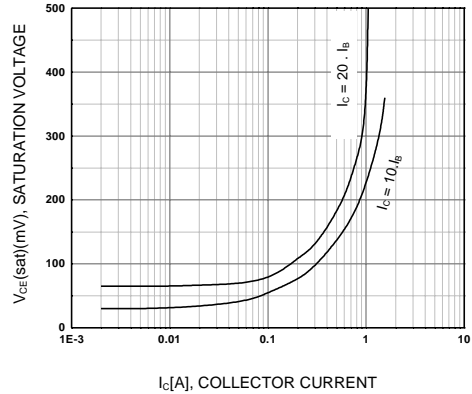


Figure 2. Collector-Emitter Saturation Voltage

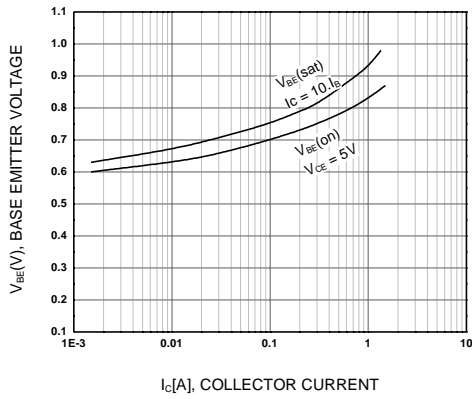


Figure 3. Base-Emitter Voltage

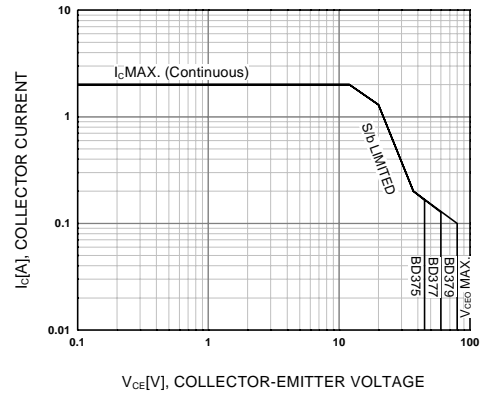


Figure 4. Safe Operating Area

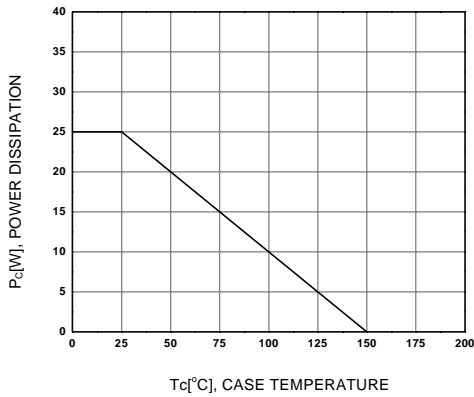


Figure 5. Power Derating

# Package Dimensions

## TO-126

BD375/377/379



Dimensions in Millimeters

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